

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild <a href="general-regarding-numbers-n

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



FQA90N15

May 2014

N-Channel QFET $^{\circledR}$ MOSFET 150 V, 90 A, 18 m Ω

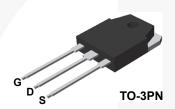
Features

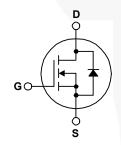
- $R_{DS(on)}$ = 18 m Ω (Max.) @ V_{GS} = 10 V, I_D = 45 A
- · Low Gate Charge (Typ. 220 nC)
- · Low Crss (Typ. 200 pF)
- · 100% Avalanche Tested
- 175°C Maximum Junction Memperature Rating

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as audio amplifier, high efficiency switching for DC/DC converters, and DC motor control, uninterrupted power supply.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

9					
Symbol		Parameter		FQA90N15	Unit
V _{DSS}	Drain-Source Voltage		/-	150	V
I _D	Drain Current	- Continuous (T _C = 25°C - Continuous (T _C = 100°		90 63.5	A A
I _{DM}	Drain Current	- Pulsed	(Note 1)	360	Α
V _{GSS}	Gate-Source voltage			±25	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		(Note 2)	1400	mJ
I _{AR}	Avalanche Current (Note		(Note 1)	90	Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		(Note 1)	37.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		(Note 3)	6.0	V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate Above 25°C			375 2.5	W W/°C
T _{J,} T _{STG}	Operating and Storage Temperature Range			-55 to +175	°C
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		oose,	300	°C

Thermal Characteristics

Symbol	Parameter	FQA90N15	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.4	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA90N15	FQA90N15	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
Off Charac	teristics			ı		I
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	150			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	-	0.15		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	Zero Gate Voltage Drain Current V_{DS} = 150V, V_{GS} = 0V V_{DS} = 120V, V_{CS} = 150°C			1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 25V, V _{DS} = 0V	-		100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -25V, V _{DS} = 0V	-		-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 45A		0.014	0.018	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40V, I _D = 45A	-	68		S
Dynamic C	Characteristics			•	•	
C _{iss}	Input Capacitance $V_{DS} = 25V, V_{GS} = 0V,$		\	6700	8700	pF
C _{oss}	Output Capacitance	f = 1.0MHz	-	1400	1800	pF
C _{rss}	Reverse Transfer Capacitance		-	200	260	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 75V, I _D = 90A		105	220	ns
t _r	Turn-On Rise Time	$R_G = 25\Omega$		760	1500	ns
t _{d(off)}	Turn-Off Delay Time		-	470	950	ns
t _f	Turn-Off Fall Time	(Note 4)	-	410	830	ns
Qg	Total Gate Charge	V _{DS} = 120V, I _D = 90A	/	220	285	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10V	/	43		nC
Q_{gd}	Gate-Drain Charge (Note 4)		74	110		nC
Drain-Sour	rce Diode Characteristics and Maximur	n Ratings	1	I	Ż	
I _S Maximum Continuous Drain-Source Diode Forward Current					90	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				360	Α
V_{SD}	Drain-Source Diode Forward Voltage V _{GS} = 0V, I _S = 90A				1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 90A		175		ns
Q _{rr}	Reverse Recovery Charge	dl _F /dt =100A/μs		0.97		μС

NOTES

^{1.} Repetitive rating: pulse-width limited by maximum junction temperature.

^{2.} L = 0.29 mH, I_{AS} = 90 A, V_{DD} = 25 V, R_G = 25 Ω , starting T_J = 25°C.

 $^{3.}I_{SD} \leq 90$ A, di/dt ≤ 300 A/µs, $V_{DD} \leq BV_{DSS}$, starting T_J = 25°C.

^{4.} Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

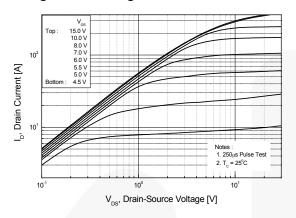


Figure 2. Transfer Characteristics

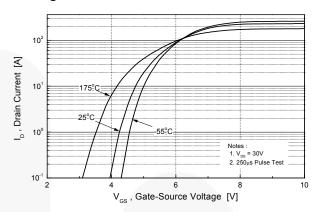


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

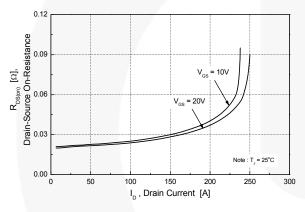


Figure 4. Body Diode Forward Voltage Variation vs. Source Current

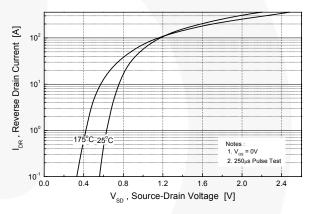


Figure 5. Capacitance Characteristics

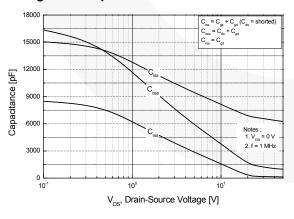
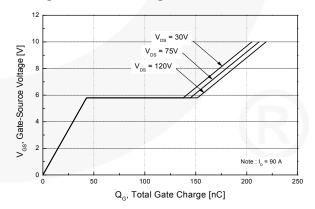


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

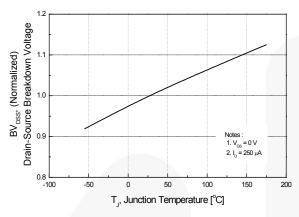


Figure 8. On-Resistance Variation vs. Temperature

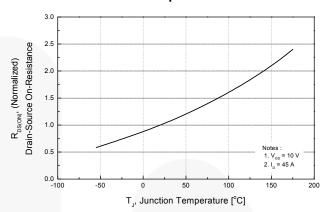


Figure 9. Maximum Safe Operating Area

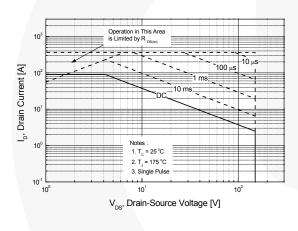


Figure 10. Maximum Drain Current vs. Case Temperature

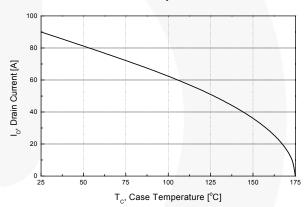
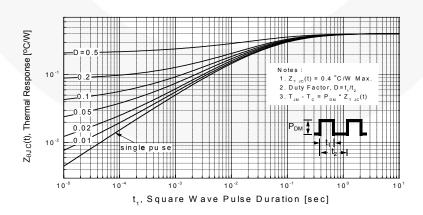


Figure 11. Transient Thermal Response Curve



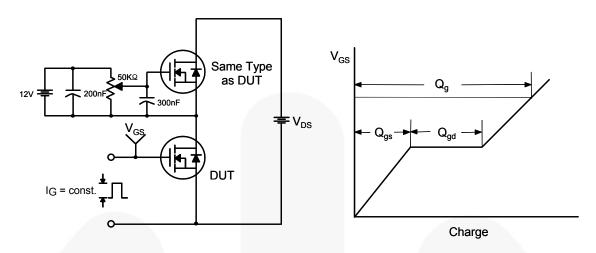


Figure 12. Gate Charge Test Circuit & Waveform

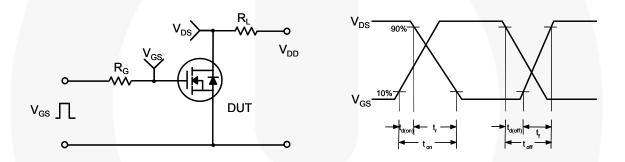


Figure 13. Resistive Switching Test Circuit & Waveforms

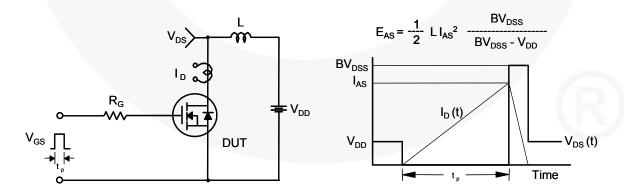


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

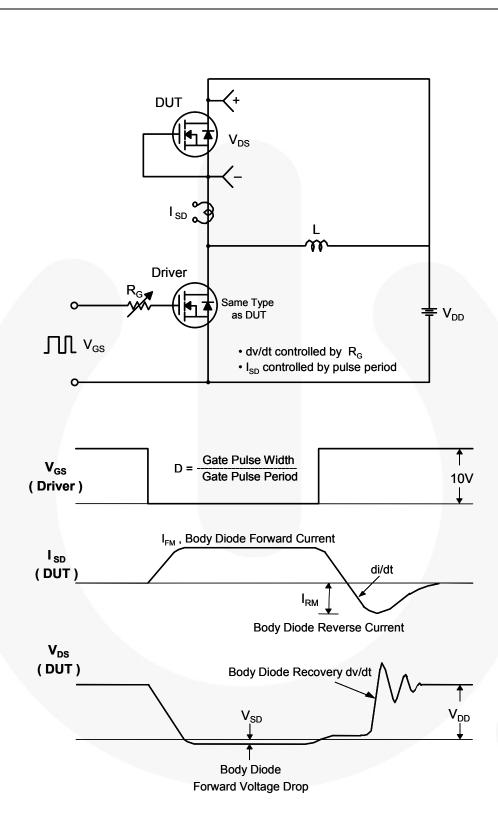
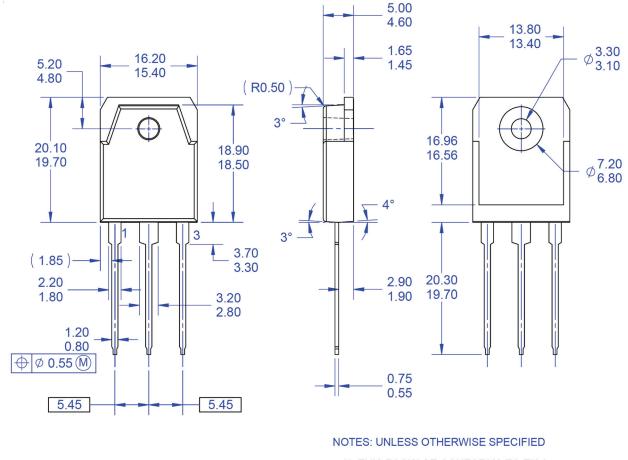
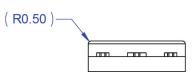


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
 E) DRAWING FILE NAME: TO3PN03AREV1.
- FAIRCHILD SEMICONDUCTOR.

Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT3PN-003





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™
AX-CAP®*
BitSiC™
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™

CTL™
Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EfficentMax™
ESBC™

Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™
FPS™

F-PFS™ FRFET®

Global Power ResourceSM GreenBridge[™]

Green FPS™ Green FPS™ e-Series™

Gmax[™] GTO[™] IntelliMAX[™] ISOPLANAR[™]

Marking Small Speakers Sound Louder and Better $^{\text{TM}}$

Marking Small Speak and Better™ MegaBuck™ MICROCOUPLER™ MicroFET™ MicroPak™ MicroPak2™ MillerDrive™ MotionMax™

MicroPak2 IM
MillerDrive TM
MotionMax TM
mWSaver®
OptoHiT TM
OPTOLOGIC®
OPTOPLANAR®

® PowerTrench® PowerXS™

Programmable Active Droop™ QFET®

QS™ Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™ SignalWise™ SmartMax™ SMART START™

Solutions for Your Success™

SPM[®] STEALTH™

SuperFET®
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS®
SyncFET™
Sync-Lock™

SYSTEM ®*
GENERAL
TinyBoost®
TinyBuck®
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™

TranSiC™
TriFault Detect™
TRUECURRENT®*
μSerDes™

K Ser Des

UHC[®]
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™
仏童™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are
 intended for surgical implant into the body or (b) support or sustain life,
 and (c) whose failure to perform when properly used in accordance with
 instructions for use provided in the labeling, can be reasonably
 expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers by either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification Product Status		Definition		
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.		
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.		

Rev. 168

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B